

CdS
 0,143 - . -
 CdS
 0,3 . 2,423 , CdS
 - 2,427 .
 CdS 550-850 (80-95) %.
 " " -
 CdS/CdTe.
 CdS 0,3 .

: 1. Martinez M.A., Herrero J., Gutierrez M.T. Properties of RF sputtered zinc oxide based thin films made from different targets // Solar Energy Materials and Solar Cells. -1994. - P. 489-498.

: 539.216:546.28'26

. . . , . - .
 -
 -
 , ,
 .
 ,
 ,
 ,
 -
 -
 -
 .[1,2]
 SiC -
 (1200°) .
 (~8%)
 , SiC. -

[1]

SiC

(~800°). [1]

: 1.

-2003.- . 10.- . 113-120. 2. Mehregany M., Zorman C.A., Roy S. Silicon carbide for microelectromechanical systems // International Materials Reviews.-2000.-V.45.- 3.- .85-105.

621.47:578.12

CdTe

()

(. [1]).

CdS/CdTe.

16,5 %,

[2].

CdS/CdTe,